

DOCUMENT CHANGE REQUEST

DCR number 685 Changes required for: N/A Originator: Benoit Cornanguer

Date: 2011/12/06 Date sent: 2011/10/26 Organisation: STMicroelectronics

Status: IM	PLEMENTED			
Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH100N6			
Number:	5205/022	Issue:	1	
Other docum	nents affected:	•		
Page:				
pages 10 &	11			
Paragraph:				
Paragraph 2	2.5.1 Room Temperature Electrical M	easurements		
Original wor	ding:			
Qgs: maxim Qgd: minim td(on): maxi tr: maximum td(off): maxi	f the AC test parameters [Qgs-Qgd-tonum limit=43nC instead of 33nC um limit=34nC instead of 39nC imum limit=34ns instead of 33.5ns in limit=140ns instead of 135ns imum limit=110ns instead of 93ns limit=45ns instead of 62ns	d(on)-tr-td(off)-tf]	need to be upda	ated as defined below:
Proposed w	ording:			
Justification	:			
The ESCC	detail specification has been written f		erization results.	(1) 1 1 (1) TO 05111

All AC electrical test parameters during the characterization phase have been done near of the body of the TO-254AA package.

Unlike for the ESCC qualification we have used a test socket; in this case we lost performance for the switching times and gate charge due to that the measurements are done more far of the body of the package.

If we take into account this statement, we are sure to cover all customer applications by giving to them the worst limits.

(This is not the case if we keep the limits defined after the characterization).

Attachments:
N/A
Modifications:
N/A
Approval signature:
12. Carlaria
Date signed:
2011-12-06